arXiv:1512.00875v2 [cond-mat.str-el] 16 Dec 2015

Bad-Metallic Behavior of Doped Mott Insulators

Jure Kokalj
J. Stefan Institute, SI-1000 Ljubljana, Slovenia and
Faculty of Civil and Geodetic Engineering, University of Ljubljana, SI-1000 Ljubljana, Slovenia

Employing Nernst-Einstein decomposition $\sigma = e^2\chi_c D$ of the conductivity σ onto charge susceptibility (compressibility) χ_c and diffusion constant D, we argue that the bad-metallic behavior of σ in the regime of high temperatures and lightly doped insulator is dominated by the strong temperature and doping dependence of χ_c. In particular, we show how at small dopings χ_c strongly decreases towards undoped-insulating values with increasing temperature and discuss simple picture leading to the linear-in-temperature resistivity with the prefactor increasing inversely with decreasing concentration (p) of doped holes, $\rho \propto T/p$. On the other hand, D shows weak temperature and doping dependence in the corresponding regime. We support our arguments by numerical results on the prototypical two dimensional Hubbard model and discuss the proposed picture at length from the experimental point of view.

PACS numbers: 71.27.+a, 71.30.+h, 71.10.Fd

Introduction. Many materials show puzzling bad-metallic behavior in which resistivity is linear-in-temperature up to very high temperatures, e.g. $\sim$ 1000 K, and in addition smoothly crosses the Mott-Ioffe-Regel (MIR) limit without any indication [1]. Understanding this behavior is one of the central challenges of solid state physics ever since its discovery [2] in the cuprate high-temperature superconductors, in particular since it might be the key towards understanding the superconductivity. Bad-metallic behavior is observed also in may other classes of materials like pnictides [3–5], fullerenes [6], vanadium dioxide [7], ruthenates [8], organic charge transfer salts [9] and nickelates [10].

Despite this ubiquitous behavior, consensus on its proper understanding is still missing. In 1970s it has been discussed in terms or electron-phonon scattering [11, 12], followed by discussion of strong electron-electron interactions and correlations [1, 13, 14], while more recent proposals include quantum criticality [15–17] and a bound on diffusion constant motivated by holographic duality [18].

We use the Nernst-Einstein relation

$$\sigma = e^2\chi_c D, \tag{1}$$

which relates conductivity σ to the charge susceptibility (compressibility) $\chi_c = \partial n/\partial\mu$ and diffusion constant D. e is electronic charge, n is electronic density and μ is chemical potential. We argue that in the high temperature (T) regime of the doped insulators linear-in-T resistivity arrises due to strong T dependence of $\chi_c \propto 1/T$ and is therefore a static effect. On the other hand, D shows weak T dependence and due to its relation to the scattering rate $1/\tau$, suggest that also $1/\tau$ has weak T-dependence. In addition we show, that at small dopings χ_c gets strongly suppressed with increasing T, due to approaching insulating values, which strongly increases the resistivity $\rho = 1/\sigma$. This naturally leads to the resistivity crossing the Mott-Ioffe-Regel (MIR) limit. We also show that χ_c has strong doping dependence and discuss how it is influenced by the antiferromagnetic (AFM) correlations of the Mott insulator.

Discussion of Nernst-Einstein relation. Eq. (1) deconstructs σ onto χ_c and D. $\chi_c(= \partial n/\partial\mu)$ measures the change of electronic density due to changes of chemical potential and since μ plays essentially the same role as a static uniform electric potential $e\phi$ [19], χ_c can be seen as the measure of how strong is the tension of the system to redistribute electronic density in the presence of slowly varying external electric potential. In the usual band and Mott-Hubbard insulators $\chi_c = 0$ (at least at $T = 0$) and hence $\sigma = 0$ or $\rho = \infty$. A particularly interesting situation appears for doped antiferromagnetic Mott-insulators, where in the insulator $\chi_c = 0$, while with doping a transition from antiferromagnet to metal appears with discontinuos jump or divergence of n vs. μ ($\chi_c = \infty$). These two extreme limits of χ_c very close in the phase diagram can lead to strong temperature and doping dependence of χ_c and in turn of ρ, simply due to T-broadening effect. On the other hand, if χ_c measures the tension for charge redistribution in the presence of external potential, D describes the rate at which the electron density redistributes and is therefore a dynamic quantity, e.g., it is related to the mean square velocity $\langle v^2\rangle$ and the scattering rate, $D = \langle v^2\rangle\tau/2$.

Hubbard model results. To explore the behavior of χ_c and D of doped insulators we use Hubbard model on a two dimensional lattice as a prototype model allowing for description of insulating phase (with possibility of AFM ordering) as well as of metallic doped insulator. The model Hamiltonian is

$$H = -t\sum_{\langle i,j\rangle,s}(c^\dagger_{i,s}c_{j,s} + \text{h.c.}) + U\sum_i n_{i,\uparrow}n_{i,\downarrow} - \mu\sum_{i,s} n_{i,s}. \tag{2}$$

t is the hopping amplitude, $c_{i,s}$ ($c^\dagger_{i,s}$) is the annihilation (creation) operator of electron on site i with spin s ($\uparrow$ or $\downarrow$), $\langle i,j\rangle$ denotes nearest-neighbor sites on a lattice (we focus only on a square and triangular lattice), U is the onsite Coulomb repulsion and $n_{i,s} = c^\dagger_{i,s}c_{i,s}$. We use units $\hbar = k_B = 1$. We evaluate quantities for this model by using numerical Finite-temperature Lanczos method (FTLM) [13, 20] on finite clusters (16 sites), which allows precise evaluation of physical properties at high T and is therefore suitable to tackle these questions. However, at low T finite-size effects appear.

In Fig. 1a we show $n(\mu)$ calculated on a square lattice for

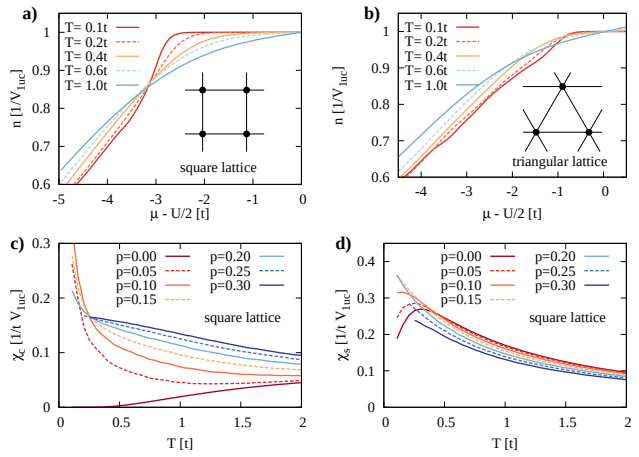

Figure 1. Electron density n vs. chemical potential μ and charge susceptibility ($\chi_c = \partial n/\partial\mu$) show strong T dependence at low dopings of Mott insulator. In addition, results suggest that χ_c is at low dopings increased by AFM correlations. **a)** n vs. μ for several T and square lattice, showing gapped behavior at $n = 1$ and finite slope at finite dopings ($n < 1$) with particularly large slope at small dopings. **b)** n vs. μ for several T and for triangular lattice, showing smaller slope at finite dopings than square lattice. This suggest χ_c at low dopings can be increased by AFM correlations, which are larger for square lattice than for frustrated triangular one. This is further supported by comparison of panel **c**), which shows χ_c vs. T for several doping and its increase at low T and low doping, with panel **d**), which shows in the same regime suppressed uniform spin susceptibility χ_s. This suppression is due to stronger AFM correlations [21]. Results are calculated for $U = 10t$ and $V_{1\text{uc}}$ denotes one-unit-cell volume.

several T and for $U = 10t$, which is within an insulating regime for half-filling ($n = 1$). At low $T \sim 0.1t$ a gapped behavior with $\chi_c = \partial n/\partial\mu = 0$ is observed at $n = 1$, while at finite hole dopings χ_c is finite. With increasing T the dependence of n on μ is smoothed. At half-filling ($n = 1$) the behavior of χ_c is activated obtaining finite values at T comparable to the charge gap Δ_c (see Fig. 1c and Ref. 20). On the other hand, it is particularly evident that for small dopings ($n = 0.95$, $p = 1 - n = 0.05$) χ_c gets strongly reduced with increasing T and that μ is rapidly moved into the gapped regime for low T. This strong T dependence of χ_c is reflected in strong T dependence of ρ as shown below in Fig. 2. Such behavior originates in the following. For small dopings the increase of T populates states according to the Boltzmann statistics and the states at half-filling and smaller density ($n \leq 1$) are relatively low in energy considering μ for chosen p and can therefore be easily populated, while states with $n > 1$ are higher in energy for about a charge gap Δ_c and cannot be efficiently populated for $T < \Delta_c$. Therefore the only way for the system to conserve the number of electrons with increasing T is to move μ into the gap and increasingly populate the half-filled ($n = 1$) states. From this, one can expect that in this T regime the behavior of the doped system will approach the behavior of the gapped one with increasing T. We stress that this situation appears for any doped charge-gapped system, as long as the density of electrons is conserved (e.g. semiconductor, band insulator, Mott insulator, etc.).

χ_c of a lightly doped Mott insulator has additional feature in contrast to, e.g., semiconductor or band insulator. At $T = 0$ and for $U \ll t$ the increase of U for δU leads to the increase of Δ_c at $n = 1$ to roughly $\Delta_c + \delta U$, but due to the same increase of μ_{max} at which the band is completely filled ($n = 2$) to $\mu_{\text{max}} + \delta U$, such increase of U does not (at least on average) change χ_c for finite dopings ($n \neq 1$). The effect of strong AFM correlations is different. The appearance of AFM correlations decreases the energy of Mott-insulating state for an order of exchange energy J, makes it more stable and increases Δ_c. For fixed U and in turn fixed μ_{max} as well as μ_{min}, this needs to be accompanied with the increase of χ_c for $n \neq 1$. This is seen in Fig. 1a and 1c at low dopings (e.g. $p \sim 0.05$) and at low T ($\sim 0.1t$). Such increase of χ_c does not appear in a triangular lattice as shown in Fig. 1b, since AFM correlations or magnetic moments are decreased due to spin frustration. Our results in Fig. 1 are in agreement with numerical results on square lattice [13, 21–24] showing the divergence (or tendency for it) of χ_c at the MIT and with the absence of such divergence for fully frustrated triangular t-J model [25]. It has also been shown that introduction of (spin frustrating) diagonal hopping t' reduces the divergence of χ_c and may explain differecnes in χ_c between cuprate families [26]. From this picture it is evident that AFM correlations can influence χ_c at finite dopings as is discussed also by Imada [27]. The increase of χ_c at low dopings and T due to AFM correlations is supported also by simultaneous decrease of unifrom spin susceptibility χ_s in the same regime (see Figs. 1(c,d)) and originating in the development of AFM correlations [21]. Furthermore, χ_c may also relate to the pseudogap, as e.g. discussed by Sordi et al. [28], but the relation remains to be further clarified.

We note that similar behavior of $n(\mu)$ and χ_c as shown in Fig. 1 appears also in band insulators and semiconductors, but generally with non-diverging χ_c. Still, the diverging χ_c can be, for example, realized via the singularity in the density of states. Diverging χ_c is obtained also for AFM order within the Hartree-Fock approximation (slater insulator) [27]. On the other hand, the critical exponents can vary between these cases [27].

In the following we show that strong doping and T dependence of χ_c governs also $\rho = 1/\sigma$, as is expected from Eq. (1), in particular at high T and low dopings. We first calculate optical conductivity $\sigma(\omega)$ and extract DC conductivity $\sigma = \sigma(\omega \to 0)$ in a standard way for Hubbard model [Eq. (2)] on finite clusters via FTLM [13, 20]. This method gives exact results for large $T > T_{\text{fs}}$, while at low $T < T_{\text{fs}}$ finite size effects appear. In $\sigma(\omega)$ finite size effects appear in the form of finite charge stiffness D_c at finite T, while we know D_c should be zero due to non-integrability of the model. D_c becomes smaller with cluster size but at low T ($< T_{\text{fs}}$) the associated delta peak, $2\pi e^2 D_c \delta(\omega)$, represents considerable part of the total spectral weight. Due to some numerical uncertainty, we judge that the finite size effects in $\sigma(\omega)$ are neg-

ligible and $D_c = 0$, if the relative weight of D_c peak to the total spectral weight is less than 1% [13].

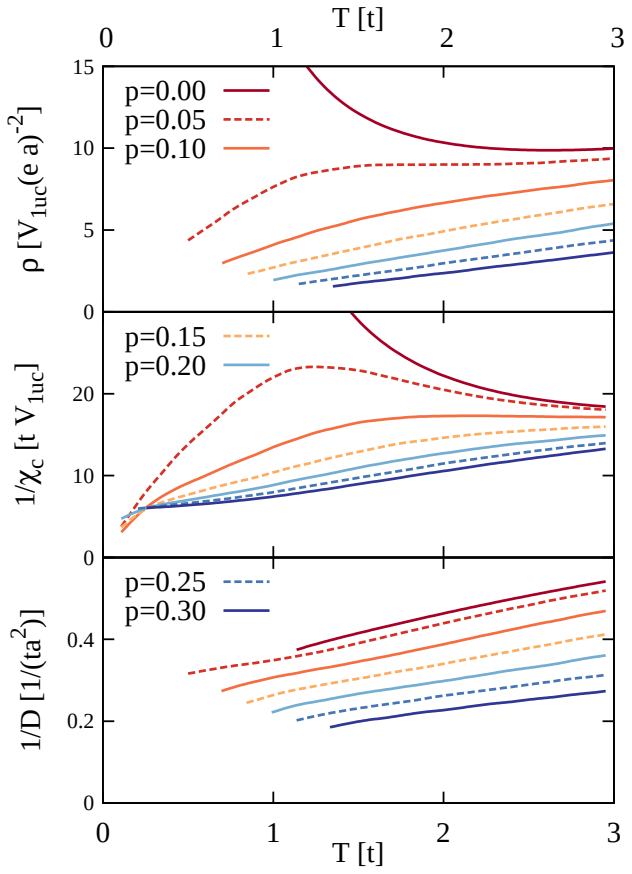

Figure 2. Resistivity ρ (upper panel) of doped Mott insulator shows strong T and doping ($p = 1 - n$) dependence at high T, and is dominated by the T and p dependence of inverse charge susceptibility $1/\chi_c$ (middle panel). $1/\chi_c$ clearly shows similar behavior as ρ. On the other hand, in the same regime diffusion constant (D) has a very weak T and p dependence. In particular, see the regime of $p = 0.05$ and $0.5t < T < t$ in which $\rho \propto T$, which originates in $1/\chi_c \propto T$ and its increase by about a factor of 2, while D increases only by about 10%. Results are calculated for square lattice with $U = 10t$ and regimes potentially influenced by finite size effects are not show.

In Fig. 2 we show T dependence of calculated ρ, $1/\chi_c$ and $1/D$, which we estimate as $1/D = \rho\chi_c/e^2$. It is clear that the T and doping (p) dependence of ρ is dominated by T and doping dependence of χ_c, while D shows rather weak and modest dependence. The most intriguing dependence of ρ and $1/\chi_c$ appears in the low-T and low-doping regime, where both quantities from small values at low T show strong and close to linear-in-T increase towards large insulating ($p = 0$) values. This originates in the move of μ into the charge gap with increasing T to conserve the density of electrons as discussed above. On the other hand, $1/D$ shows much more mundane dependence with weak increase with increasing T and small decrease with p in the whole shown regime. In the $T \to 0$ limit one expects scattering rate and $1/D$ to go to 0 and therefore to strongly influence ρ. We do not reach this regime since finite size effect appear first, but we stress that system size dependence (not shown) of our results suggest weak T dependence of D and dominance of ρ by χ_c even for lower T than shown in Fig. 2. This comes from the decrease of D_c with increasing system size (our criteria for finite size effect) in a manner that does not alter $\sigma(\omega)$ at low ω much, and for this low ω the almost T independent behavior of D shown in Fig. 2 extends to lower T, which we, e.g., estimate to $T \sim 0.2t$ for $p = 0.05$. On the other hand, finite size effects for χ_c are smaller, as indicated by showing $1/\chi_c$ to much lower T in Fig. 2. At lowest T and dopings ($p < 0.15$), $1/\chi_c$ shows additional suppression which presumably originates in the AFM correlations as discussed in Fig. 1, and could be related to the pseudogap.

From diffusion constant we can estimate the mean free path l via $D = \langle v \rangle l/2$. The estimate of average velocity $\langle v \rangle$ is not straight forward and we use the estimate $\langle v \rangle = 8ta/\pi$, which together with the values of D from Fig. 2 gives l of the order of lattice spacing, $l \sim a$. Therefore, regarding l and $1/\tau$, the MIR limit is not crossed. However, considering only ρ, the MIR limit is violated due to strong increase of $1/\chi_c$ towards the insulating values with increasing T as shown in Fig. 2. The crossing of the MIR limit without any change or indication in the resistivity has a natural explanation in our picture in terms of decreasing χ_c. And further, since there in no limit for $1/\chi_c$ close to the insulating regime ($1/\chi_c = \infty$), one does not expect an upper limit for the resistivity.

Strong T and doping dependence of χ_c shown in Fig. 2 appears for any doped insulator, including Mott insulator, band insulator and semiconductor, as long as n is fixed and not μ. However, in doped semiconductor χ_c shows two activated insulating regimes [29], e.g., at low T due to μ being in the gap between valence band ϵ_v and acceptor levels ϵ_a, while at higher T, due to μ being close to the middle of the band gap E_g. Similar behavior is observed also in ρ, but for proper relation also D should be considered, in particular, since localized doping levels contribute to χ_c but have $D = 0$. Interestingly, the regime of small doping and $\epsilon_v - \epsilon_a \ll T < E_g$ for which the chemical potential is in the charge gap E_g has the text-book [29] density of conducting valence band holes $p_v = P_v \mathrm{e}^{(\epsilon_v - \mu)/T}$, which readily leads to $\chi_c = p_v/T$. This dictates $\rho \propto T/p_v$. In semiconductor this regime of ρ can be mask by much stronger delocalizing activated (exponential) behavior, but similar relation can be expected also in doped Mott insulators, for which doped charges are itinerant and therefore strongly decrease ρ at lowest T (in contrast to semiconductors). Semiconducting picture with $p = P_v \mathrm{e}^{(\epsilon_v - \mu)/T}$ has indeed been proposed also for the cuprates [21, 30], and it leads to $1/\chi_c = T/p$. We, however stress, that our results are only close to this picture since hole doping shifts μ into the lower band, while in semiconductors it stays above the valence band maximum.

Another feature arising naturally in the proposed picture is the optical spectral weight transfer. Due to the shift of μ

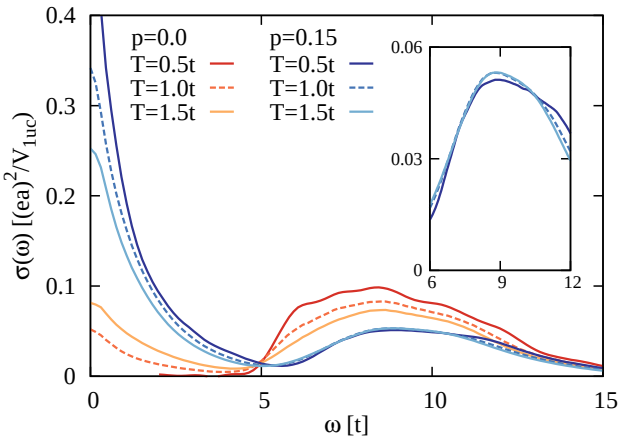

Figure 3. Real part of conductivity $\sigma(\omega)$ for two dopings ($p = 0$ and $p = 0.15$) and for several high T ($0.5t$, t and $1.5t$). $p = 0.15$ case shows spectral weight transfer from low ω to high ω (see inset) with increasing T, and is simultaneously becoming more similar to insulating case. $p = 0$ case shows opposite transfer of weight from high ω to low ω (activated behavior) with increasing T. Results are for square lattice and $U = 10t$.

into the gap with increasing T and approaching more insulating like behavior it is natural that with increasing T the optical conductivity for doped Mott insulators shows decrease of the low ω spectral weight with simultaneous increase of the higher ω spectral weight, namely the transfer to the Hubbard bands. This is shown in Fig. 3 (see also inset) for $p = 0.15$, while the data for the insulating ($p = 0$) case show opposite behavior, namely the transfer of weight from high ω to low ω with increasing T. It is also clear from Fig. 3 that with increasing T the spectra for $p = 0$ and $p = 0.15$ are becoming similar (at low and high ω). We note that some transfer, in particular the increase of spectral weight can be suppressed by the decrease of the integrated spectral weight with increasing T, which is related to the decrease of the absolute kinetic energy.

We further note that the width of the low-ω part of $\sigma(\omega)$ is related to τ via $\sigma(\omega) = \chi_c D/(1+\omega^2\tau^2)$ assuming D is ω independent and since in the bad-metallic regime both D and τ are expected to have weak T dependece, the width of the low ω part is expected to have weak T dependence within our picture. This is indeed the case for the results shown in Fig. 3. We also note that the calculation of χ_c just from a spectral function $A(k,\omega)$ is not straight forward, since also the dependence of self-energy $\Sigma(k,\omega)$ on μ needs to be know (see Ref. 19).

Experiments. It is of utmost importance to see whether experiments show any confirmation or indication of the proposed picture. We first need to determine the temperature regime where such behavior is expected. Denoting with $T_{\rm coh}$ the temperature above which χ_c has strong T dependence we estimate that $T_{\rm coh} \sim |\mu(p) - \mu_c|_{T=0}$, where $\mu(p)$ and μ_c are the $T = 0$ chemical potential at doping p and critical chemical potential for the transition to the insulating state, respectively. This leads to $T_{\rm coh} \sim p/\bar{\chi}_c$ where $\bar{\chi}_c$ is averaged χ_c between insulating $p = 0$ case and doping p at $T = 0$. $T_{\rm coh}$ goes to 0 as $p \to 0$ and we estimate $T_{\rm coh} \sim pW$ for non-diverging χ_c at the transition with W being half-band width. T_{coh} can therefore be much lower than W, e.g., for $t = 0.35$ eV and $p = 0.1$ we estimate $T_{\rm coh}$ of the order of 1000 K. However, divergent χ_c at the MIT as shown in Figs. 1 can reduce $T_{\rm coh}$ by an order of magnitude (see Fig. 2) and for the same case we than estimate $T_{\rm coh}$ of the order of 100 K. Similar picture with the estimate $T_{\rm coh} \sim t^* p^2$ (with t^* being renormalized hoping) is discussed by Imada [27], who also estimates $T_{\rm coh}$ to around 100 K for $p = 0.1$.

By using photo emission spectroscopy (PES) it is possible to measure T and p dependence of μ allowing for direct experimental estimate of χ_c. The results for cuprate (Bi2212) by Tanaka et al. (see Fig. 8.8b in Ref. 31) show strong increase of μ with increasing T already for $T \sim 200$ K, as well as strong doping dependence particularly at small dopings ($p < 0.08$). Similar data on LSCO by Harima et al. [32] show very large values of χ_c in the underdoped regime and the same was suggested also by Wu et al. [33], while those by Malaeb et al. [34] in addition suggest strong and close to linear-in-T dependence of $1/\chi_c$. All these results are in qualitative agreement with our results and more importantly suggest that ρ can indeed be strongly influenced by χ_c. Unfortunately the direct comparison of experimental ρ and χ_c as well as extraction of D is unfeasible due to large uncertainties of PES data. Also other effects can potentially influence the PES data, e.g. Madelung potential [35, 36].

Since χ_c is basic static quantity, which measures the change of electronic density also due to the presence of external electric potential it influences also many other quantities. One of them is a Thomas-Fermi screening length (l_{TF}) of the external potential, which is related to χ_c via [29] $l_{TF} \propto 1/\sqrt{\chi_c}$ and within our picture one would expect strong T and p dependence of l_{TF} in the bad-metallic regime. There is not many experimental reports on l_{TF} since in the normal metal it can be very small, even of the order of lattice spacing. Anyhow, interestingly Jenks and Tesardi [37] reported a strong increase of l_{TF} in cuprate (YBCO) already just above the superconducting transition temperature.

On the other hand one can make indirect comparison of experimental high T resistivity and our $1/\chi_c$ at least on qualitative level. Resistivity data on various cuprates [1, 38–42] show $\rho \sim aT$ in the high T regime with the prefactor a increasing with decreasing doping in good qualitative agrement with our results in Fig. 2. Similar increase of linear-in-T part of ρ has been observed also in the low-T regime [4, 43, 44], but we stress that at this low-T regime scattering rate and D are expected to give the dominant T dependence.

Behavior of ρ and χ_c shown in Fig. 2 is not expected just in above discussed Mott insulators, but also for doped band insulators. Remarkably similar doping and T dependence has been lately reported for the electrostatically doped band insulator MoS_2 [45]. Furthermore, for nickelates Jaramillo et

al. [10] observed that the bad-metallic behavior is related to the decreasing effective carrier density $n_{\rm eff}$ with increasing T while measured τ and effective mass show rather weak T dependence. This is closely related to our decreasing-in-T χ_c and weak T dependence of D.

Another feature that emerges within our picture is the spectral weight transfer in the bad-metallic regime (see Fig. 3), namely decreasing $\sigma(\omega)$ at low ω (below the charge gap) and increasing $\sigma(\omega)$ at high ω (above the charge gap or at the Hubbard bands) with increasing T. This is in qualitative agreement with optical conductivity for cuprates and many other bad-metallic materials [42, 46–48].

Conclusions. In summary we propose an explanation of high-T bad-metallic behavior with large and linear-in-T resistivity of doped insulator in terms of much simpler static quantity, namely charge susceptibility χ_c. Furthermore, since χ_c should have similar T and doping dependence for any charge insulator (with exception of insulators with spatially localized electrons, e.g., due to disorder) similar features in resistivity are expected for Mott and band insulators, semiconductors as well as AFM slater insulators. Still the details like T and doping regimes as well as possible T dependence of the charge gap can vary between different cases and materials. We further discuss that in this simple picture the coefficient of linear-in-T resistivity is close to being proportional to $1/p$ as observed in many materials, while the diffusion constant D shows weak doping and T dependence. Same holds for the mean free path, which we estimate to the order of few lattice spacing. Crossing of MIR limit observed in resistivity can be naturally understood as χ_c becoming small with increasing T due to proximity of insulating state. We note that our picture is opposite to the main suggestion that $D \propto 1/T$ by Hartnoll [18], since in our case D shows weak T dependence and is closer to the results by Pakhira and McKenzie [19]. The origin of the bad-metallic behavior is in our picture strong T dependence of χ_c, which has indeed been acknowledged as a possibility for doped insulators [18]. D and related scattering rate are expected to play important role at lower T and in the tentative Fermi liquid regime, where also mean free path is expected to increase strongly with decreasing T.

Future challenges. It remains theoretical and experimental challenge to establish in which regime of T and doping the resistivity is dominated by χ_c and in which by D. Also a regime where both contributions are important is possible. This applies also to the bandwidth controlled MIT, as e.g. realized in organics [9]. Theoretical challenge is to reach lower T and in this respect continuous improvements of the insight into the phenomena, of analytical and numerical techniques as well as computational power is promising. Importance of the static effects in the bad-metallic regime has been already advocated, e.g., in terms of quasiparticle renormalization [49] or carrier density [50], but correspondence with our picture needs to be further clarified. Our picture is also close to the one presented by Boyd et al. [51], who discusses ρ in terms of transport relaxation time, which is presumably dominated by the effective density of states, but distinct behavior of static and dynamic quantities has unfortunately not been discussed. Indication of a weak T dependence of D at higher temperatures comes also from a DMFT study [52] where a weak T dependence of the imaginary part of self-energy at elevated T was observed.

Even more important is to experimentally establish the behavior of χ_c and D with T and doping. In this respect PES, Thomas-Fermi screening length and other possibilities are invaluable. Since charge susceptibility affects screening of electric potential it can play considerable role also in phonon softening [53] and even in superconductivity [24, 27]. D has been already measured in cuprates [54], but unfortunately for nonequilibrium quasi-particles. This makes it inapplicable to our analysis. Measurements of D are very challenging but also highly desirable. Experimental deconstruction of ρ onto χ_c and D would further pose strong constraints on the theories and would differentiate between them. They would for example offer insight on the questions like; is there a quantum critical point [15, 16], is diffusion bounded as motivated by holographic duality [18], is the pseudogap a new phase [55], is the nature of the insulator Mott, band or (AFM) slater like.

Deconstruction of ρ onto χ_c and D therefore offers an exciting, promising and yet to be fully explored approach towards better understanding of discussed phenomena, both from theoretical and experimental point of view.

I acknowledge helpful discussions with Ross McKenzie, Peter Prelovšek, Takami Tohyama, Veljko Zlatić, Jernej Mravlje, Neven Barišić, Giovanni Sordi, Ivan Bozović and Joseph Orenstein. This work was supported by Slovenian Research Agency Grant No. Z1-5442 and Program P1-0044.

[1] O. Gunnarsson, M. Calandra, and J. E. Han, Rev. Mod. Phys. **75**, 1085 (2003).
[2] M. Gurvitch and A. T. Fiory, Phys. Rev. Lett. **59**, 1337 (1987).
[3] J. J. Ying, X. F. Wang, T. Wu, Z. J. Xiang, R. H. Liu, Y. J. Yan, A. F. Wang, M. Zhang, G. J. Ye, P. Cheng, J. P. Hu, and X. H. Chen, Phys. Rev. Lett. **107**, 067001 (2011).
[4] N. Doiron-Leyraud, P. Auban-Senzier, S. René de Cotret, C. Bourbonnais, D. Jérome, K. Bechgaard, and L. Taillefer, Phys. Rev. B **80**, 214531 (2009).
[5] R. H. Liu, G. Wu, T. Wu, D. F. Fang, H. Chen, S. Y. Li, K. Liu, Y. L. Xie, X. F. Wang, R. L. Yang, L. Ding, C. He, D. L. Feng, and X. H. Chen, Phys. Rev. Lett. **101**, 087001 (2008).
[6] O. Gunnarsson and J. E. Han, Nature **405**, 1027 (2000).
[7] M. M. Qazilbash, K. S. Burch, D. Whisler, D. Shrekenhamer, B. G. Chae, H. T. Kim, and D. N. Basov, Phys. Rev. B **74**, 205118 (2006).
[8] A. W. Tyler, A. P. Mackenzie, S. NishiZaki, and Y. Maeno, Phys. Rev. B **58**, R10107 (1998).
[9] B. J. Powell and R. H. McKenzie, Rep. Prog. Phys. **74**, 056501 (2011).
[10] R. Jaramillo, S. D. Ha, D. M. Silevitch, and S. Ramanathan, Nat. Phys. **10**, 304 (2014).
[11] P. Allen, *Superconductivity in d- and f-Band Metals*, edited by H. Suhl and M. B. Maple (Academic, New York, 1980).
[12] P. Allen, *Physics of Transition Metals*, edited by P. Rhodes (Inst. Phys. Conf. Ser. No. 55 (Institute of Physics, London), 1980).

[13] J. Jaklič and P. Prelovšek, Adv. Phys. **49**, 1 (2000).
[14] A. Georges, L. d. Medici, and J. Mravlje, Annu. Rev. Condens. Matter Phys. **4**, 137 (2013).
[15] S. Sachdev and B. Keimer, Phys. Today **64**, 29 (2011).
[16] D. Galanakis, E. Khatami, K. Mikelsons, A. Macridin, J. Moreno, D. A. Browne, and M. Jarrell, Phil. Trans. R. Soc. A **369**, 1670 (2011).
[17] J. Vučičević, D. Tanasković, M. J. Rozenberg, and V. Dobrosavljević, Phys. Rev. Lett. **114**, 246402 (2015).
[18] S. A. Hartnoll, Nat. Phys. **11**, 54 (2015).
[19] N. Pakhira and R. H. McKenzie, Phys. Rev. B **91**, 075124 (2015).
[20] J. Kokalj and R. H. McKenzie, Phys. Rev. Lett. **110**, 206402 (2013).
[21] J. Bonča and P. Prelovšek, Phys. Rev. B **67**, 085103 (2003).
[22] N. Furukawa and M. Imada, J. Phys. Soc. Jpn. **61**, 3331 (1992).
[23] S. Watanabe and M. Imada, J. Phys. Soc. Jpn. **73**, 1251 (2004).
[24] T. Misawa and M. Imada, Phys. Rev. B **90**, 115137 (2014).
[25] T. Tohyama, Phys. Rev. B **74**, 113108 (2006).
[26] T. Tohyama and S. Maekawa, Phys. Rev. B **67**, 092509 (2003).
[27] M. Imada, J. Phys. Soc. Jpn. **64**, 2954 (1995).
[28] G. Sordi, K. Haule, and A.-M. S. Tremblay, Phys. Rev. B **84**, 075161 (2011).
[29] N. W. Ashcroft and N. D. Mermin, *Solid State Physics* (Thomson Learning, 1976).
[30] P. Prelovšek, *Normal State Properties of Cuprates: t-J Model vs. Experiment* (Springer, 2001)
[31] K. Tanaka, *Photoemission study of Bi-cuprate high-Tc superconductors in the lightly-doped to underdoped regions* (Doctor thesis, University of Tokyo, 2004)
[32] N. Harima, J. Matsuno, A. Fujimori, Y. Onose, Y. Taguchi, and Y. Tokura, Phys. Rev. B **64**, 220507 (2001).
[33] J. Wu, O. Pelleg, G. Logvenov, A. T. Bollinger, Y.-J. Sun, G. S. Boebinger, M. Vanevi, Z. Radovi, and I. Boovi, Nat. Mater. **12**, 877 (2013).
[34] W. Malaeb, T. Yoshida, M. Hashimoto, M. Takizawa, K. Ebata, A. Fujimori, H. Eisaki, T. Kakeshita, T. Sasagawa, and S. Uchida, JPCS **108**, 012018 (2008).
[35] A. Fujimori, A. Ino, J. Matsuno, T. Yoshida, K. Tanaka, and T. Mizokawa, J. Electron. Spectrosc. Relat. Phenom. **124**, 127 (2002).
[36] M. Ikeda, M. Takizawa, T. Yoshida, A. Fujimori, K. Segawa, and Y. Ando, Phys. Rev. B **82** (2010).
[37] W. G. Jenks and L. R. Testardi, Phys. Rev. B **48**, 12993 (1993).
[38] H. Takagi, B. Batlogg, H. L. Kao, J. Kwo, R. J. Cava, J. J. Krajewski, and W. F. Peck, Phys. Rev. Lett. **69**, 2975 (1992).
[39] T. Ito, K. Takenaka, and S. Uchida, Phys. Rev. Lett. **70**, 3995 (1993).
[40] Y. Onose, Y. Taguchi, K. Ishizaka, and Y. Tokura, Phys. Rev. B **69**, 024504 (2004).
[41] P. L. Bach, S. R. Saha, K. Kirshenbaum, J. Paglione, and R. L. Greene, Phys. Rev. B **83**, 212506 (2011).
[42] D. Nicoletti, P. D. Pietro, O. Limaj, P. Calvani, U. Schade, S. Ono, Y. Ando, and S. Lupi, New J. Phys. **13**, 123009 (2011).
[43] N. Barišić, M. K. Chan, Y. Li, G. Yu, X. Zhao, M. Dressel, A. Smontara, and M. Greven, PNAS **110**, 12235 (2013).
[44] J. Kokalj, N. E. Hussey, and R. H. McKenzie, Phys. Rev. B **86**, 045132 (2012).
[45] J. T. Ye, Y. J. Zhang, R. Akashi, M. S. Bahramy, R. Arita, and Y. Iwasa, Science **338**, 1193 (2012).
[46] K. Takenaka, J. Nohara, R. Shiozaki, and S. Sugai, Phys. Rev. B **68**, 134501 (2003).
[47] N. E. Hussey, K. Takenaka, and H. Takagi, Philos. Mag. **84**, 2847 (2004).
[48] P. Phillips, Rev. Mod. Phys. **82**, 1719 (2010).
[49] W. Xu, K. Haule, and G. Kotliar, Phys. Rev. Lett. **111**, 036401 (2013).
[50] N. Barišić, M. K. Chan, M. J. Veit, C. J. Dorow, Y. Ge, Y. Tang, W. Tabis, G. Yu, X. Zhao, and M. Greven, arXiv:1507.07885 [cond-mat] (2015).
[51] G. R. Boyd, V. Zlatić, and J. K. Freericks, Phys. Rev. B **91**, 075118 (2015).
[52] X. Deng, J. Mravlje, R. Žitko, M. Ferrero, G. Kotliar, and A. Georges, Phys. Rev. Lett. **110**, 086401 (2013).
[53] M. V. Eremin and M. A. Malakhov, JETP Letters **100**, 324 (2014).
[54] N. Gedik, J. Orenstein, R. Liang, D. A. Bonn, and W. N. Hardy, Science **300**, 1410 (2003).
[55] Y. Li, V. Balédent, G. Yu, N. Barišić, K. Hradil, R. A. Mole, Y. Sidis, P. Steffens, X. Zhao, P. Bourges, and M. Greven, Nature **468**, 283 (2010).